

What is claimed is:

1. A plating method, comprising:

filling a plating liquid containing metal ions and an additive

5 into a plating space formed between a substrate and an anode disposed closely to the substrate so as to face the substrate; and

changing the concentration of the additive in the plating liquid filled into said plating space during a plating process.

10 2. The plating method according to claim 1, wherein the concentration of the additive in the plating liquid is adjusted by intermittently supplying the plating liquid into said plating space.

15 3. The plating method according to claim 1, wherein the concentration of the additive in the plating liquid is adjusted by supplementary addition of the additive to said plating space.

20 4. The plating method according to claim 1, wherein the concentration of the additive in the plating liquid is adjusted by removal of the additive in the plating liquid.

25 5. The plating method according to claim 1, wherein the additive is a brightener, and the concentration of the brightener at the middle and later stages of the plating process is lower than that at the initial stage of the plating process.

6. The plating method according to claim 1, wherein the

additive is a leveler, and the concentration of the leveler at the middle and later stages of the plating process is higher than that at the initial stage of the plating process.

- 5 7. A plating apparatus, comprising:
 a substrate holder for holding a substrate so that a current
can flow from a cathode to the substrate;
 an anode opposed to the substrate held by said substrate
holder; and
10 a plating liquid introducing device for introducing a plating
liquid into a plating space formed between the substrate and said
anode in a batch process or an intermittent process.

- 15 8. The plating apparatus according to claim 7, wherein a
plating liquid impregnation material is provided in said plating
space.

- 20 9. The plating apparatus according to claim 7, further
comprising a liquid introducing device for introducing into said
plating space a liquid having a different additive concentration
from the additive concentration of the plating liquid.

- 25 10. The plating apparatus according to claim 9, wherein a
plating liquid impregnation material is provided in said plating
space.

11. The plating apparatus according to claim 7, further
comprising a temperature adjusting device for adjusting the

temperature of the plating liquid in said plating space.

12. A plating apparatus, comprising:

a substrate holder for holding a substrate so that a current

5 can flow from a cathode to the substrate;

an anode opposed to the substrate held by said substrate
holder; and

10 a moving device for moving a portion of the substrate facing
said anode in such a state that an inner central portion of the
surface of the substrate faces said anode for a longer time than
an outer peripheral portion of the surface of the substrate faces
said anode.

13. The plating apparatus according to claim 12, wherein said

15 moving device comprises a substrate-rotating device for rotating
the substrate.

14. The plating apparatus according to claim 12, wherein said
moving device comprises an anode-rotating device for rotating said
20 anode.

15. The plating apparatus according to claim 12, wherein said
moving device comprises an anode-translating device for
translating said anode.

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16. A plating apparatus, comprising:

a substrate holder for holding a substrate so that a current
can flow from a cathode to the substrate; and

an anode opposed to the substrate held by said substrate holder,

wherein the distance between said anode and an inner central portion of the substrate is smaller than the distance between said anode and an outer peripheral portion of the substrate.

5 17. A plating apparatus, comprising:

a substrate holder for holding a substrate so that a current can flow from a cathode to the substrate;

10 an anode opposed to the substrate held by said substrate holder; and

a distance changing device for changing the distance between the substrate and said anode after initiation of plating.

15 18. A plating method, comprising:

disposing a substrate and an anode in such a state that the substrate faces said anode;

flowing a current between the substrate and said anode while supplying a plating liquid therebetween; and

20 moving a portion of the substrate facing said anode in such a state that an inner central portion of the surface of the substrate faces said anode for a longer time than an outer peripheral portion of the surface of the substrate faces said anode.

25 19. The plating method according to claim 18, wherein the portion of the substrate facing said anode is moved by rotation of the substrate.

20. The plating method according to claim 18, wherein the portion of the substrate facing said anode is moved by rotation of said anode.

5 21. The plating method according to claim 18, wherein the portion of the substrate facing said anode is moved by translation of said anode.

22. A plating method, comprising:

10 disposing a substrate and an anode so that the substrate faces said substrate; and

 flowing a current between the substrate and said anode while supplying a plating liquid therebetween,

15 wherein the distance between said anode and an inner central portion of the substrate is smaller than the distance between said anode and an outer peripheral portion of the substrate.

23. A plating method, comprising:

20 disposing a substrate and an anode so that the substrate faces said anode;

 flowing a current between the substrate and said anode while supplying a plating liquid therebetween; and

 changing the distance between the substrate and said anode after initiation of plating.